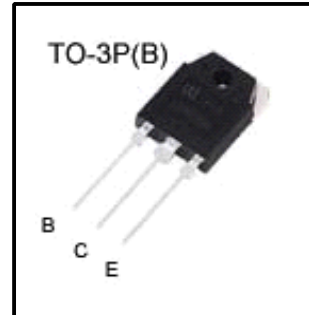


## *High voltage Fast Switching NPN Power Transistor*

### Features

- Very High Switching Speed
- High voltage Capability
- Wide Reverse Bias SOA



### General Description

This Device is designed for high voltage, High speed switching characteristics required such as lighting system, switching mode power supply.

### Absolute Maximum Ratings

| Symbol    | Parameter                             | Test Conditions | Value   | Units      |
|-----------|---------------------------------------|-----------------|---------|------------|
| $V_{CES}$ | Collector -Emitter Voltage            | $V_{BE}=0$      | 700     | V          |
| $V_{CEO}$ | Collector -Emitter Voltage            | $I_B=0$         | 400     | V          |
| $V_{EBO}$ | Emitter -Base Voltage                 | $I_C=0$         | 9.0     | V          |
| $I_C$     | Collector Current                     |                 | 12      | A          |
| $I_{CP}$  | Collector pulse Current               |                 | 25      | A          |
| $I_B$     | Base Current                          |                 | 6.0     | A          |
| $I_{BM}$  | Base Peak Current                     | $t_p=5ms$       | 12      | A          |
| $P_C$     | Total Dissipation at $T_c=25^\circ C$ |                 | 110     | W          |
| $T_J$     | Operation Junction Temperature        |                 | -40~150 | $^\circ C$ |
| $T_{STG}$ | Storage Temperature                   |                 | -40~150 | $^\circ C$ |

### Thermal Characteristics

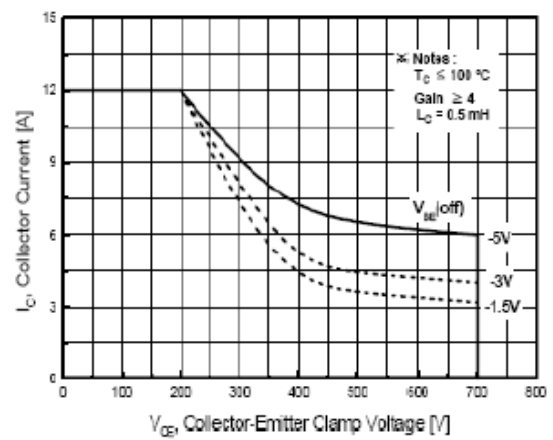
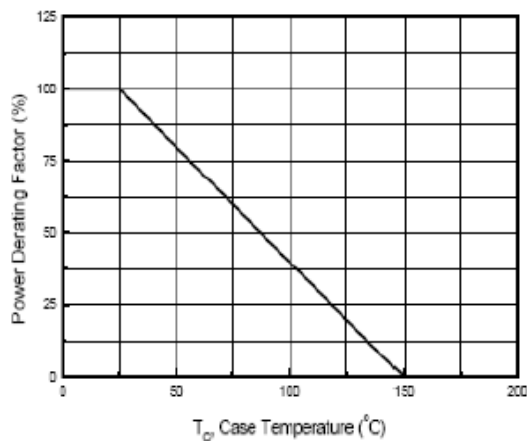
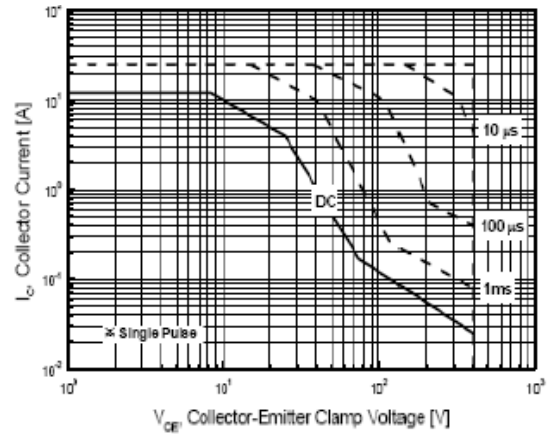
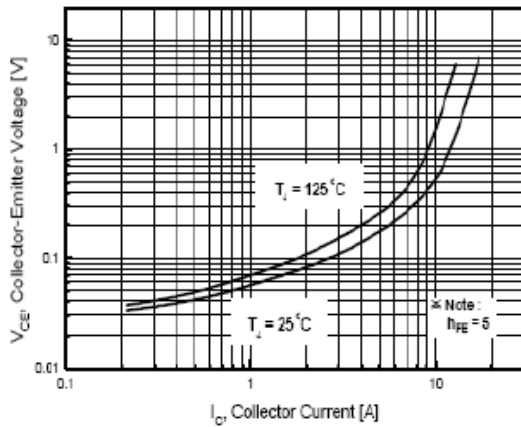
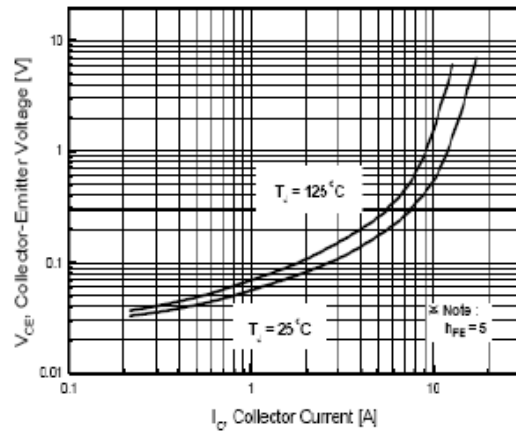
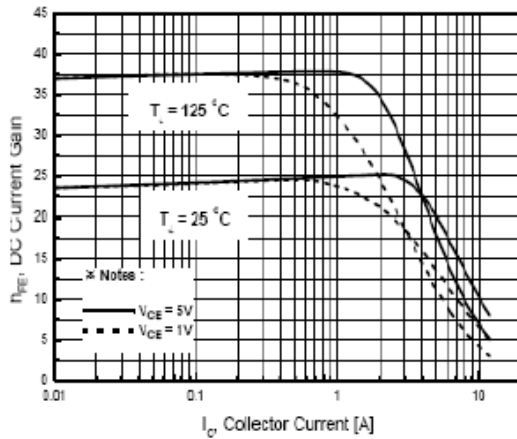
| Symbol          | Parameter                              | Value | Units        |
|-----------------|----------------------------------------|-------|--------------|
| $R_{\theta JC}$ | Thermal Resistance Junction to Case    | 1.13  | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance Junction to Ambient | 62.5  | $^\circ C/W$ |

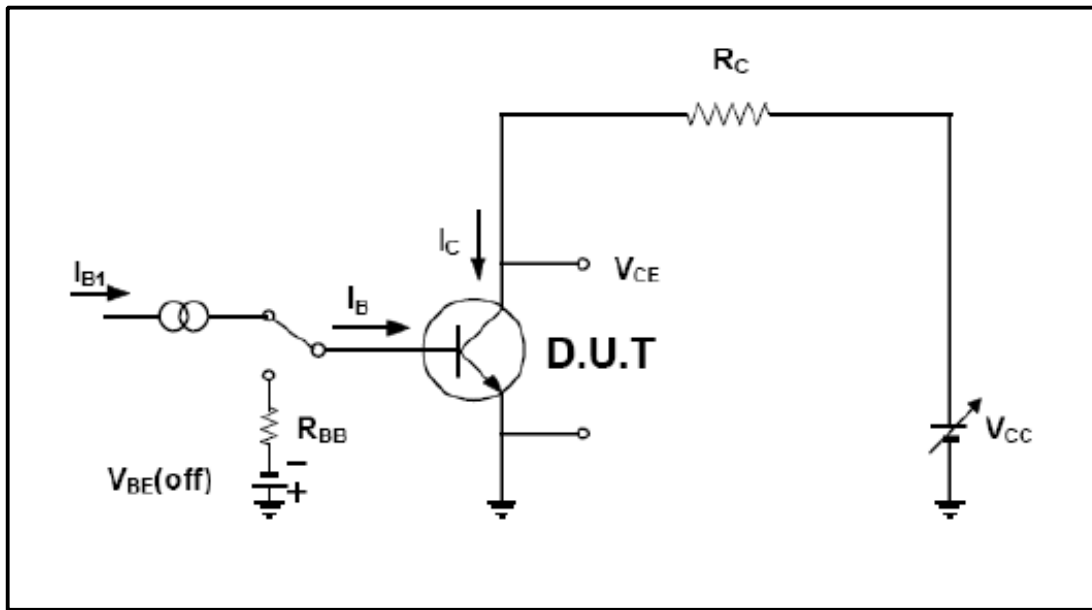
**Electrical Characteristics**

| Symbol        | Parameter                            | Test conditions                                                     | Value |     |                   | Units   |
|---------------|--------------------------------------|---------------------------------------------------------------------|-------|-----|-------------------|---------|
|               |                                      |                                                                     | Min   | Typ | Max               |         |
| $V_{CE(sus)}$ | Collector-Emitter Breakdown Voltage  | $I_c=10mA, I_b=0$                                                   | 400   | -   | -                 | V       |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_c=5.0A, I_b=1.0A$<br>$I_c=8.0A, I_b=1.6A$<br>$I_c=12A, I_b=3.0A$ | -     | -   | 1.0<br>1.5<br>3.0 | V       |
|               |                                      | $I_c=8.0A, I_b=1.6A$<br>$T_c=100^\circ C$                           | -     | -   | 2.0               | V       |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage      | $I_c=5.0A, I_b=1.0A$<br>$I_c=8.0A, I_b=1.6A$                        | -     | -   | 1.2<br>1.6        | V       |
|               |                                      | $I_c=8.0A, I_b=1.6A$<br>$T_c=100^\circ C$                           | -     | -   | 1.5               | V       |
| $I_{EBO}$     | Emitter -Base Cutoff Current         | $V_{eb}=9V, I_c=0V$                                                 | -     | -   | 10                | $\mu A$ |
| hFE           | DC Current Gain                      | $V_{ce}=5V, I_c=5.0A$                                               | 10    | -   | 40                |         |
|               |                                      | $V_{ce}=5V, I_c=8.0A$                                               | 6     | -   | 30                |         |
| $t_s$         | Storage Time                         | $V_{cc}=5.0V, I_c=0.5A$                                             | 4     | -   | 10                | $\mu s$ |
| $t_f$         | Fall Time                            | (UI9600)                                                            |       | -   | 0.8               |         |
| $f_T$         | Current Gain Band width Product      | $V_{ce}=10V, I_c=0.5A$                                              | 4     |     |                   | MHz     |

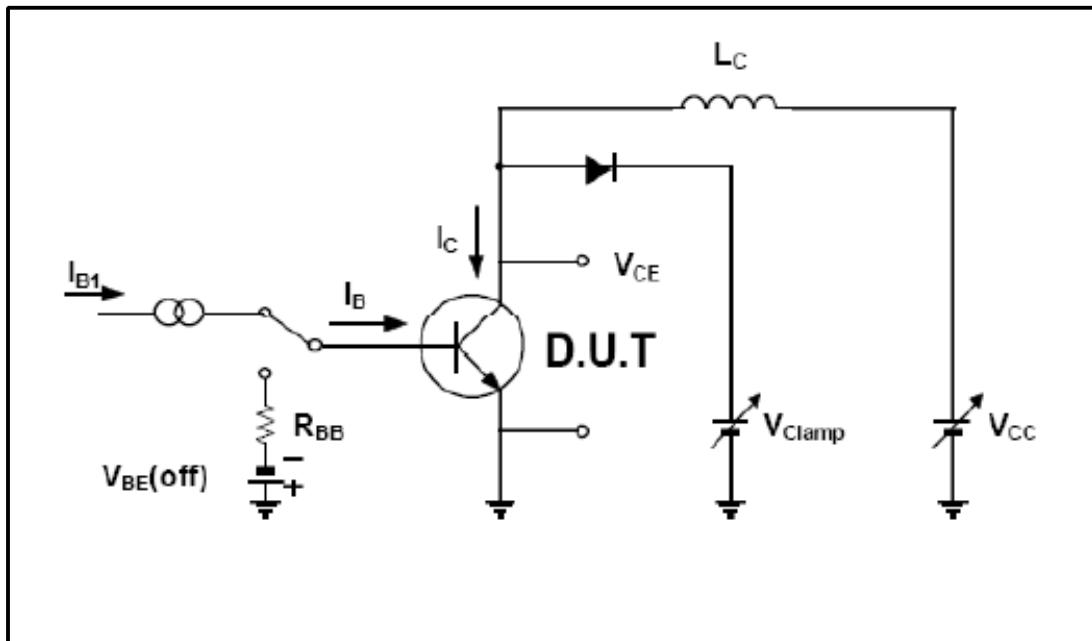
Note :

Pulse Test :Pulse width 300,Duty cycle 2%





**Resistive Load Switching Test Circuit**



**Inductive Load Switching & RBSOA Test Circuit**

**TO3P(B)Package Dimension**

